

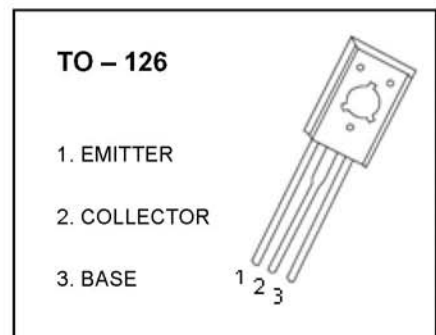
BD139 TO-126 Plastic-Encapsulate Transistors BD135/137/139 TRANSISTOR NPN

FEATURES

- High Current
- Complement To BD136, BD138 And BD140

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	BD135	45
		BD137	60
		BD139	80
V_{CEO}	Collector-Emitter Voltage	BD135	45
		BD137	60
		BD139	80
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	1.5	A
P_C	Collector Power Dissipation	1.25	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	100	$^{\circ}\text{C/W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=0.1\text{mA}, I_E=0$	BD135	45		V
			BD137	60		
			BD139	80		
Collector-emitter sustaining voltage	$V_{CEO(SUS)}$	$I_C=0.03\text{A}, I_B=0$	BD135	45		V
			BD137	60		
			BD139	80		
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=0.1\text{mA}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=30\text{V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			10	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=2\text{V}, I_C=150\text{mA}$	40		250	
	$h_{FE(2)}$	$V_{CE}=2\text{V}, I_C=5\text{mA}$	25			
	$h_{FE(3)}$	$V_{CE}=2\text{V}, I_C=500\text{mA}$	25			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500\text{mA}, I_B=50\text{mA}$			0.5	V
Base-emitter voltage	V_{BE}	$V_{CE}=2\text{V}, I_C=500\text{mA}$			1	V

*Pulse test: pulse width $\leq 350\mu\text{s}$, duty cycles $\leq 2.0\%$.

CLASSIFICATION OF $h_{FE(1)}$

RANK	6	10	16
RANGE	40-100	63-160	100-250